Dopant evaluation in 4 H-SiC by Backside SIMS

Backside SIMS is known as a useful technique to reduce the degradation of the depth resolution. Here, we show an example of the depth profiling of Al in 4H-SiC by backside SIMS.

1. Backside SIMS

Backside SIMS ...

Backside SIMS is a technique to analyze the depth profiling of elements toward the sample surface from the rear side. This technique suppresses the Knock-on effect, and the degradation of the depth resolution caused by the roughness on the sample surface generated by primary ion beams.



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